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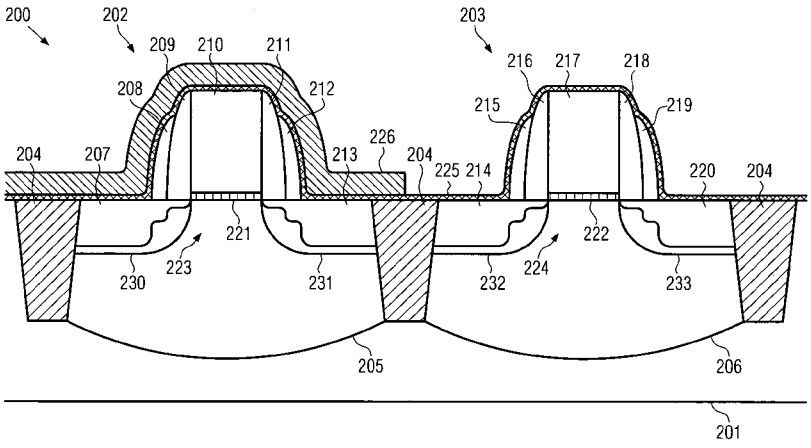
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(54) **Title:** METHOD OF FORMING A SEMICONDUCTOR STRUCTURE COMPRISING A FIELD EFFECT TRANSISTOR HAVING A STRESSED CHANNEL REGION



(57) **Abstract:** A method of forming a semiconductor structure comprises providing a semiconductor substrate comprising a first transistor element and a second transistor element. The first transistor element comprises at least one first amorphous region and the second transistor element comprises at least one second amorphous region. A stress-creating layer is formed over the first transistor element. The stress-creating layer does not cover the second transistor element. A first annealing process is performed. The first annealing process is adapted to re-crystallize the first amorphous region and the second amorphous region. After the first annealing process, a second annealing process is performed. The stress-creating layer remains on the semiconductor substrate during the second annealing process.

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